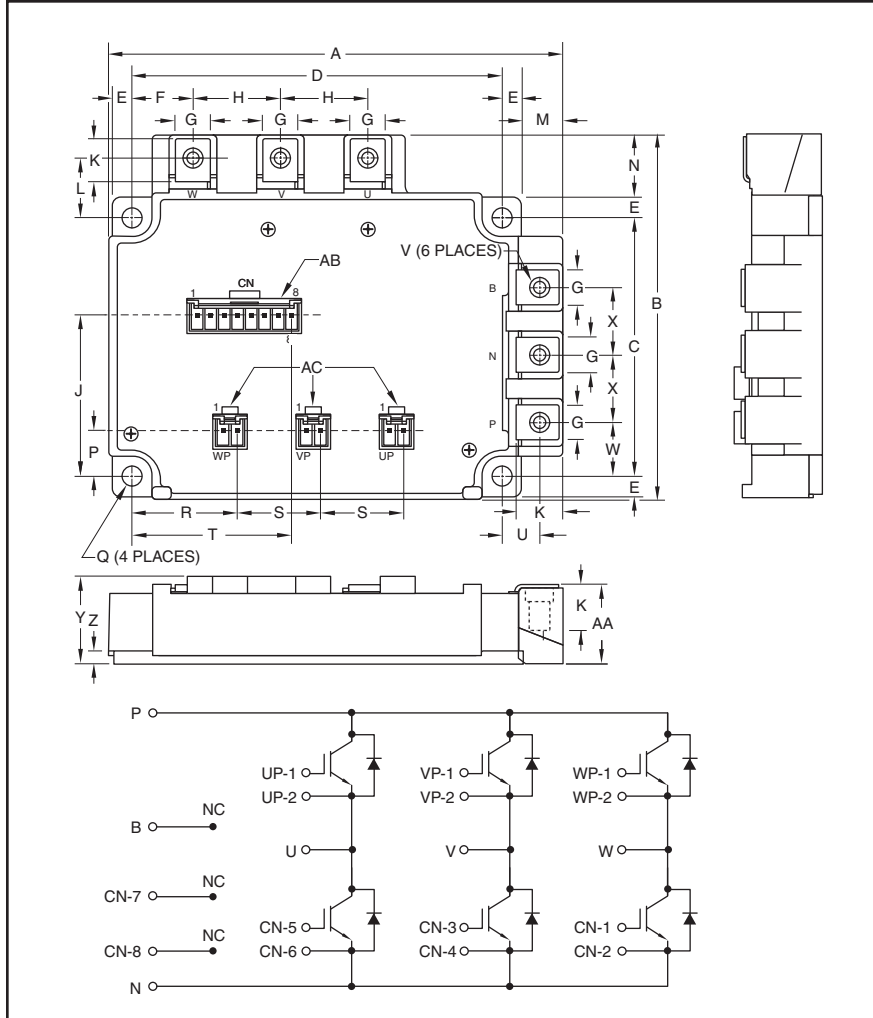


Six IGBTMOD™ NF-Series Module 150 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	5.32	135.0
B	4.33	110.0
C	3.07±0.02	78.0±0.5
D	4.33±0.02	110.0±0.5
E	0.24	6.05
F	0.69	17.5
G	0.41	10.5
H	1.02	26.0
J	1.92	48.75
K	0.51	13.0
L	0.71	18.0
M	0.46	11.7

Dimensions	Inches	Millimeters
N	0.74	18.7
P	0.54	13.75
Q	0.22	5.5 Dia.
R	1.20	30.5
S	0.98	25.0
T	1.82	46.3
U	0.43	11.0
V	M5	M5
W	0.65	16.5
X	0.78	20.0
Y	1.04	26.5
Z	0.16	4.0
AA	0.95+0.04/-0.0	24.1+1.0/-0.0

Housing Types (J.S.T. Mfg. Co. Ltd.)

AB – B8P-VH-FB-B
AC – B2P-VH-FB-B



Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of six IGBT Transistors in a three phase bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Low Drive Power
- Low $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- Isolated Baseplate for Easy Heat Sinking

Applications:

- AC Motor Control
- Motion/Servo Control
- UPS
- Photovoltaic/Fuel Cell

Ordering Information:

Example: Select the complete module number you desire from the table below -i.e. CM150TL-24NF is a 1200V (V_{CES}), 150 Ampere Six-IGBTMOD™ Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	150	24

CM150TL-24NF
Six IGBTMOD™ NF-Series Module
 150 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	CM150TL-24NF	Units
Power Device Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E Short)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E Short)	V_{GES}	± 20	Volts
Collector Current (DC, $T_C = 76^\circ\text{C}$)*4	I_C	150	Amperes
Peak Collector Current (Pulse, Repetitive)*2	I_{CM}	300	Amperes
Emitter Current (DC, $T_C = 25^\circ\text{C}$)*4	I_E^{*1}	150	Amperes
Peak Emitter Current (Pulse, Repetitive)*2	I_{EM}^{*1}	300	Amperes
Maximum Collector Dissipation ($T_C = 25^\circ\text{C}$)*2,*4	P_C	890	Watts
Mounting Torque, M5 Mounting Screws	—	31	in-lb
Mounting Torque, M5 Main Terminal Screws	—	31	in-lb
Module Weight (Typical)	—	750	Grams
Isolation Voltage, AC 1 minute, 60Hz Sinusoidal	V_{ISO}	2500	Volts

Electrical and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector Cutoff Current	I_{CES}	$V_{\text{CE}} = V_{\text{CES}}, V_{\text{GE}} = 0\text{V}$	—	—	1.0	mA
Gate-Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$I_C = 15\text{mA}, V_{\text{CE}} = 10\text{V}$	6	7	8	Volts
Gate Leakage Current	I_{GES}	$\pm V_{\text{GE}} = V_{\text{GES}}, V_{\text{CE}} = 0\text{V}$	—	—	0.5	μA
Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	$I_C = 150\text{A}, V_{\text{GE}} = 15\text{V}, T_j = 25^\circ\text{C}^{*3}$	—	2.1	3.0	Volts
		$I_C = 150\text{A}, V_{\text{GE}} = 15\text{V}, T_j = 125^\circ\text{C}^{*3}$	—	2.4	—	Volts
Forward Transfer Admittance	$ y_{\text{fs}} $	$I_C = 150\text{A}, V_{\text{CE}} = 10\text{V}^{*3}$	45	—	—	sec
Input Capacitance	C_{ies}		—	—	23.0	nf
Output Capacitance	C_{oes}	$V_{\text{CE}} = 10\text{V}, V_{\text{GE}} = 0\text{V}$	—	—	2.0	nf
Reverse Transfer Capacitance	C_{res}		—	—	0.45	nf
Total Gate Charge	Q_G	$V_{\text{CC}} = 600\text{V}, I_C = 150\text{A}, V_{\text{GE}} = 15\text{V}$	—	675	—	nC
Inductive	Turn-on Delay Time	$t_{\text{d(on)}}$	—	—	130	ns
Load	Turn-on Rise Time	t_r			70	ns
Switch	Turn-off Delay Time	$t_{\text{d(off)}}$			400	ns
Reverse Recovery Time*1	t_{rr}	Inductive Load Switching Operation	—	—	150	ns
Reverse Recovery Charge*1	Q_{rr}		—	5.8	—	μC
Emitter-Collector Voltage*1	V_{EC}	$I_E = 150\text{A}, V_{\text{GE}} = 0\text{V}$	—	—	3.8	Volts

*1 $I_E, I_{\text{EM}}, V_{\text{EC}}, t_{\text{rr}}$, and Q_{rr} represent characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

*2 Pulse width and repetition rate should be such that device junction temperature (T_j) does not exceed $T_{j(\text{max})}$ rating.

*3 Pulse width and repetition rate should be such as to cause negligible temperature rise.

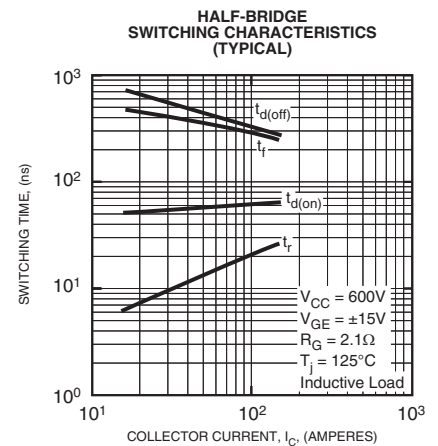
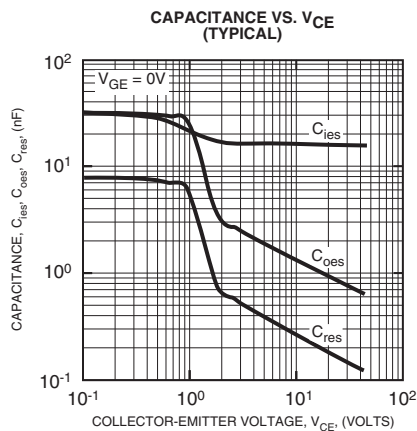
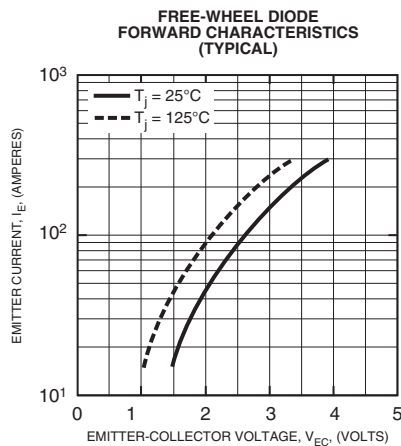
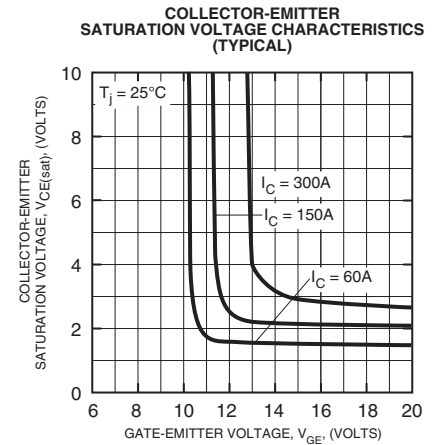
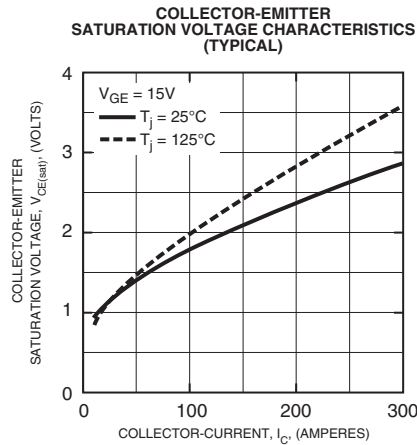
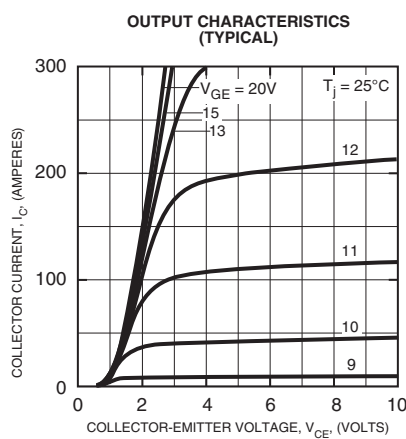
*4 T_C measured point is just under the chips.

CM150TL-24NF
Six IGBTMOD™ NF-Series Module
 150 Amperes/1200 Volts

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

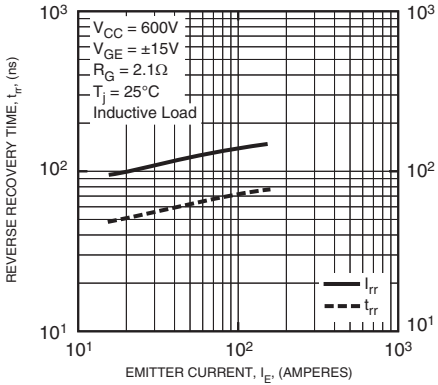
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case*	$R_{th(j-c)Q}$	Per IGBT 1/6 Module*4	—	—	0.14	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case*	$R_{th(j-c)D}$	Per FWDi 1/6 Module*4	—	—	0.23	$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per 1/6 Module, Thermal Grease Applied*4	—	0.051	—	$^\circ\text{C/W}$
External Gate Resistance	R_G		2.1	—	31	Ω

*4 T_C , T_f measured point is just under the chips.

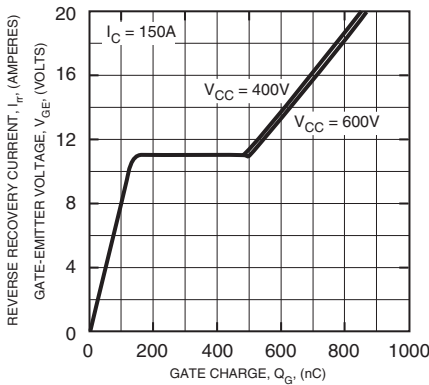


CM150TL-24NF
Six IGBTMOD™ NF-Series Module
 150 Amperes/1200 Volts

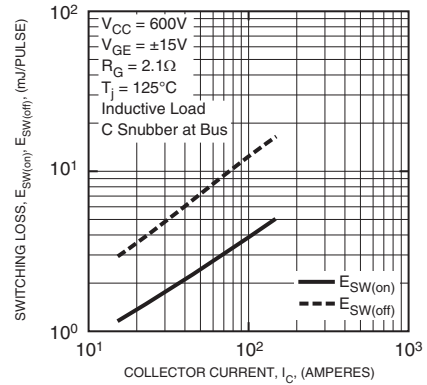
REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



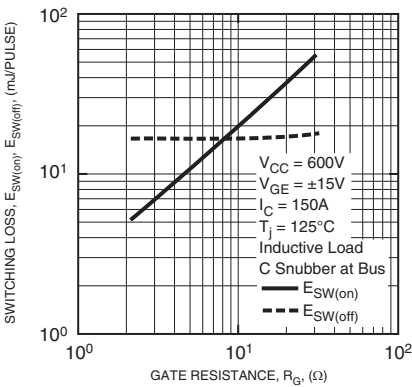
GATE CHARGE VS. V_{GE}



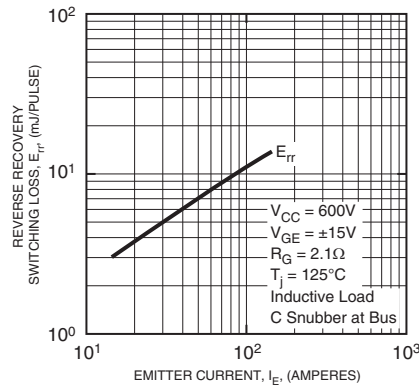
SWITCHING LOSS VS. COLLECTOR CURRENT (TYPICAL)



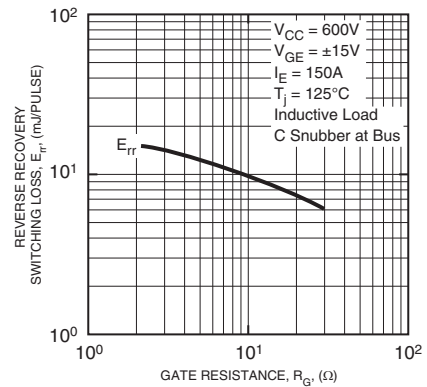
SWITCHING LOSS VS. GATE RESISTANCE (TYPICAL)



REVERSE RECOVERY SWITCHING LOSS VS. EMITTER CURRENT (TYPICAL)



REVERSE RECOVERY SWITCHING LOSS VS. GATE RESISTANCE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT & FWDI)

